

16 A Three-quadrant triacs high commutation Rev. 01 — 19 April 2007

Product data sheet

Product profile 1.

1.1 General description

Passivated, new generation, high commutation triacs in a SOT404 plastic single-ended surface-mountable package

1.2 Features

Very high commutation performance High immunity to dV/dt maximized at each gate sensitivity

1.3 Applications

- High power motor control e.g. washing Refrigeration and air conditioning machines and vacuum cleaners
- Non-linear rectifier-fed motor loads

1.4 Quick reference data

- V_{DRM} \leq 600 V (BTA316B-600B/C/E)
- V_{DRM} ≤ 800 V (BTA316B-800B/C/E)
- I_{TSM} \leq 140 A (t = 20 ms)
- I $I_{T(RMS)} \le 16 \text{ A} (t = 20 \text{ ms})$

- compressors
- Electronic thermostats
- I_{GT} \leq 50 mA (BTA316B series B)
- I_{GT} \leq 35 mA (BTA316B series C)
- IGT \leq 10 mA (BTA316B series E)

Pinning information 2.

Table 1.	Pinning		
Pin	Description	Simplified outline	Symbol
1	main terminal 1 (T1)		ς.
2	main terminal 2 (T2)	mb	T2-T1
3	gate (G)		sym051
mb	mounting base; main terminal 2 (T2)		

SOT404 (D2PAK)



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3. Ordering information

Type number	Package								
	Name	Description	Version						
BTA316B-600B	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3-leads (one lead	SOT404						
BTA316B-600C		cropped)							
BTA316B-600E									
BTA316B-800B									
BTA316B-800C									
BTA316B-800E									

4. Limiting values

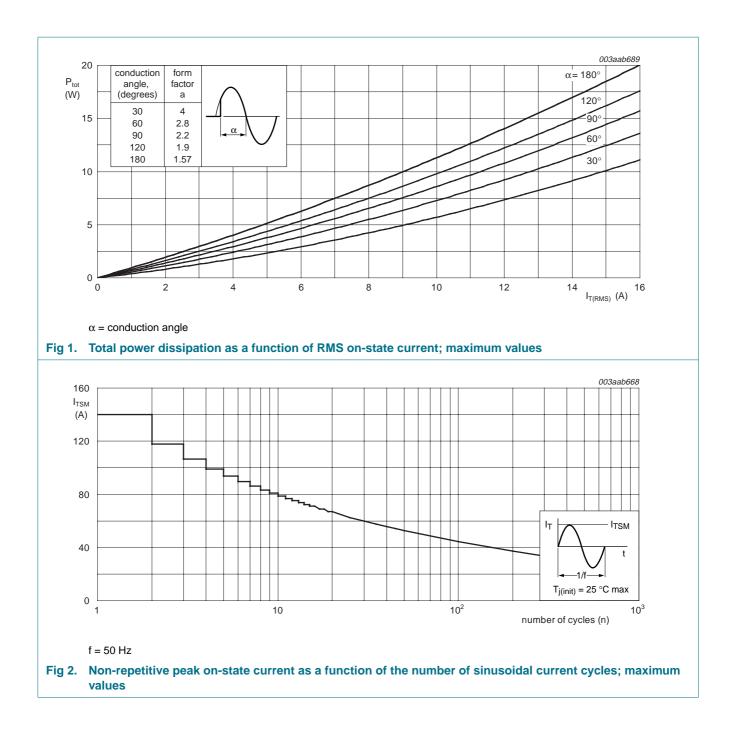
Table 3. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

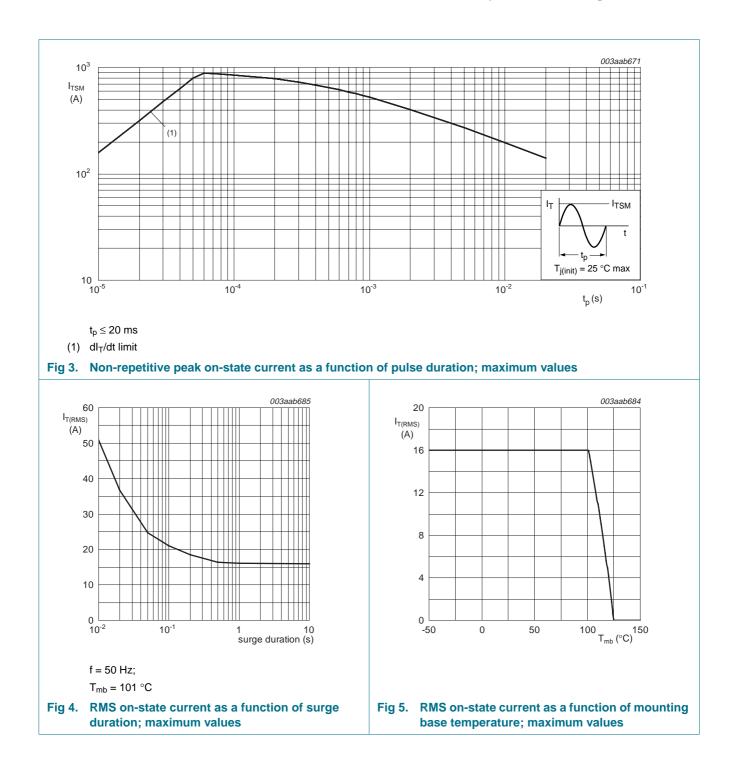
Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage	BTA316B-600B; BTA316B-600C; BTA316B-600E	<u>[1]</u> -	600	V
		BTA316B-800B; BTA316B-800C; BTA316B-800E	-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{mb} \le 101 \text{ °C}$; see Figure 4 and 5	-	16	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_j = 25 \text{ °C prior to}$ surge; see <u>Figure 2</u> and <u>3</u>			
		t = 20 ms	-	140	А
		t = 16.7 ms	-	150	А
l ² t	I ² t for fusing	t = 10 ms	-	98	A ² s
dl _T /dt	rate of rise of on-state current	$I_{TM} = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A}/\mu \text{s}$	-	100	A/μs
I _{GM}	peak gate current		-	2	А
P _{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.5	W
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	125	°C

[1] Although not recommended, off-state voltages up to 800 V may be applied without damage, but the triac may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.

BTA316B series B, C and E



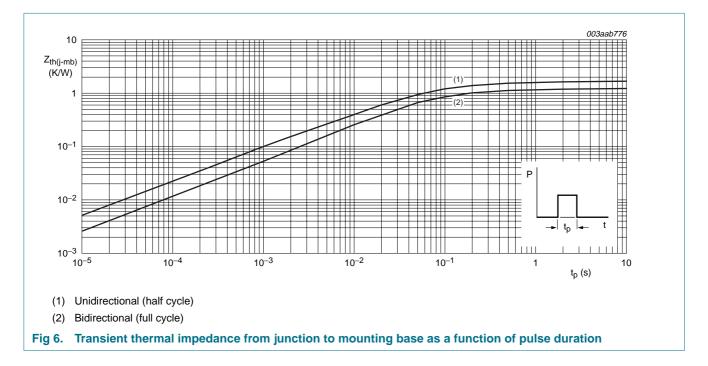
BTA316B series B, C and E



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5. Thermal characteristics

Table 4.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)} thermal resistance from junction		half cycle; see Figure 6	-	-	1.7	K/W
	mounting base	full cycle; see Figure 6	-	-	1.2	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	mounted on a printed circuit board; minimum footprint	-	55	-	K/W



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6. Static characteristics

Table 5. Static characteristics

 $T_i = 25 \circ C$ unless otherwise specified.

Symbol	Parameter	Conditions		A316B- A316B-			BTA316B-600C BTA316B-800C			BTA316B-600E BTA316B-800E		
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
I _{GT} gate trigger current		V _D = 12 V; I _T = 0.1 A; see <u>Figure 8</u>										
		T2+ G+	2	-	50	2	-	35	-	-	10	mA
		T2+ G–	2	-	50	2	-	35	-	-	10	mA
		T2– G–	2	-	50	2	-	35	-	-	10	mA
IL	latching current	$V_D = 12 V;$ I _{GT} = 0.1 A; see <u>Figure 10</u>										
		T2+ G+	-	-	60	-	-	50	-	-	25	mA
		T2+ G–	-	-	90	-	-	60	-	-	30	mA
		T2– G–	-	-	60	-	-	50	-	-	30	mA
I _H	holding current	$V_D = 12 V;$ I _{GT} = 0.1 A; see <u>Figure 11</u>	-	-	60	-	-	35	-	-	15	mA
V _T	on-state voltage	I _T = 18 A; see <u>Figure 9</u>	-	1.3	1.5	-	1.3	1.5	-	1.3	1.5	V
V _{GT}	gate trigger voltage	$V_D = 12 V;$ $I_T = 0.1 A;$ see <u>Figure 7</u>	-	0.8	1.5	-	0.8	1.5	-	0.8	1.5	V
		$V_D = 400 V;$ $I_T = 0.1 A;$ $T_j = 125 \ ^{\circ}C$	0.25	0.4	-	0.25	0.4	-	0.25	0.4	-	V
I _D	off-state current	$V_D = V_{DRM(max)};$ $T_j = 125 \ ^{\circ}C$	-	0.1	0.5	-	0.1	0.5	-	0.1	0.5	mA

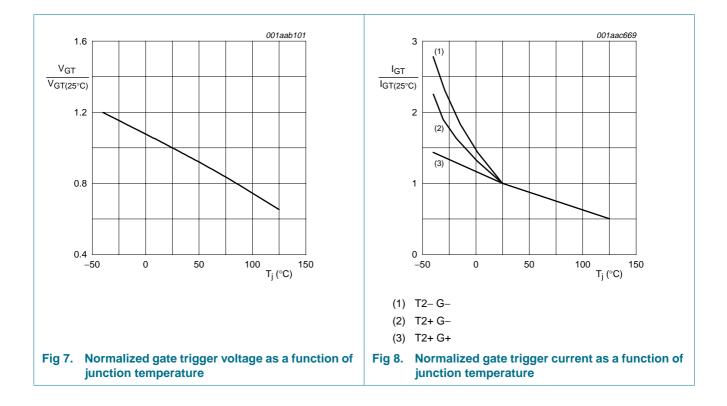
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7. Dynamic characteristics

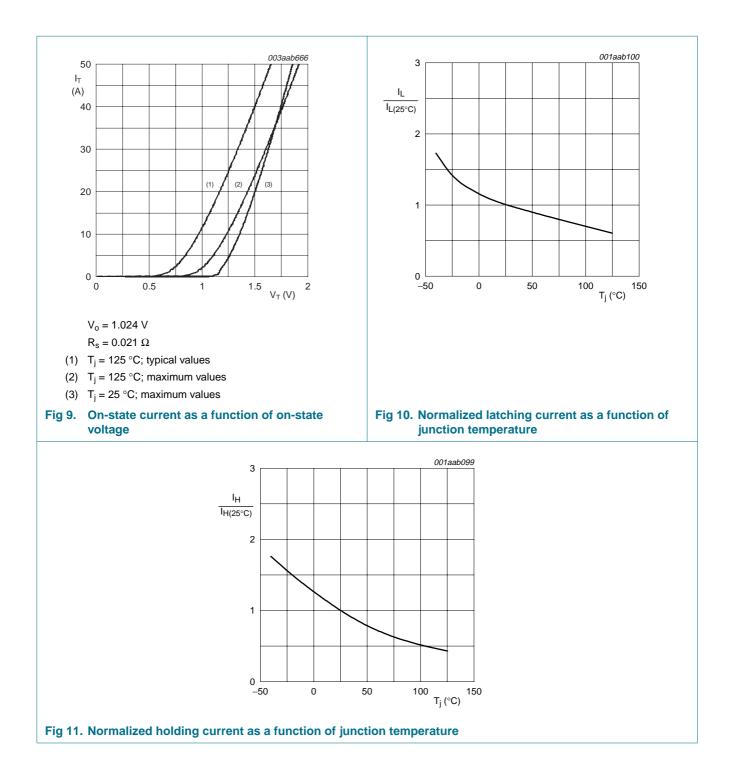
Symbol	Parameter	Conditions		BTA316B-600B BTA316B-800B		BTA316B-600C BTA316B-800C			BTA316B-600E BTA316B-800E			Unit
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
dV _D /dt	rate of rise of off-state voltage	$\begin{split} V_{DM} &= 0.67 \times \\ V_{DRM(max)}; \\ T_{j} &= 125 \ ^{\circ}C; \\ exponential \\ waveform; gate open \\ circuit \end{split}$	1000	-	-	500	-	-	60	-	-	V/µs
0 C	rate of change of commutating current	$\label{eq:VDM} \begin{array}{l} V_{DM} = 400 \text{ V}; \\ T_j = 125 \ ^\circ\text{C}; \\ I_{T(RMS)} = 16 \text{ A}; \\ \text{without snubber}; \\ \text{gate open circuit} \end{array}$	20	-	-	15	-	-	5	-	-	A/ms
		$\label{eq:VDM} \begin{array}{l} V_{DM} = 400 \text{ V}; \\ T_j = 125 \ ^\circ\text{C}; \\ I_{T(RMS)} = 16 \text{ A}; \\ dV/dt = 10 \ V/\mu\text{s}; \\ \text{gate open circuit} \end{array}$	-	-	-	-	-	-	8	-	-	A/ms
		$\label{eq:VDM} \begin{array}{l} V_{DM} = 400 \text{ V}; \\ T_j = 125 \ ^\circ\text{C}; \\ I_{T(RMS)} = 16 \text{ A}; \\ dV/dt = 1 \ V/\mu\text{s}; \ \text{gate} \\ \text{open circuit} \end{array}$	-	-	-	-	-	-	12	-	-	A/ms
t _{gt}	gate-controlled turn-on time	$I_{TM} = 20 \text{ A};$ $V_D = V_{DRM(max)};$ $I_G = 0.1 \text{ A};$ $dI_G/dt = 5 \text{ A}/\mu \text{s}$	-	2	-	-	2	-	-	2	-	μs

BTA316B_SER_B_C_E_1

BTA316B series B, C and E



BTA316B series B, C and E



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8. Package outline

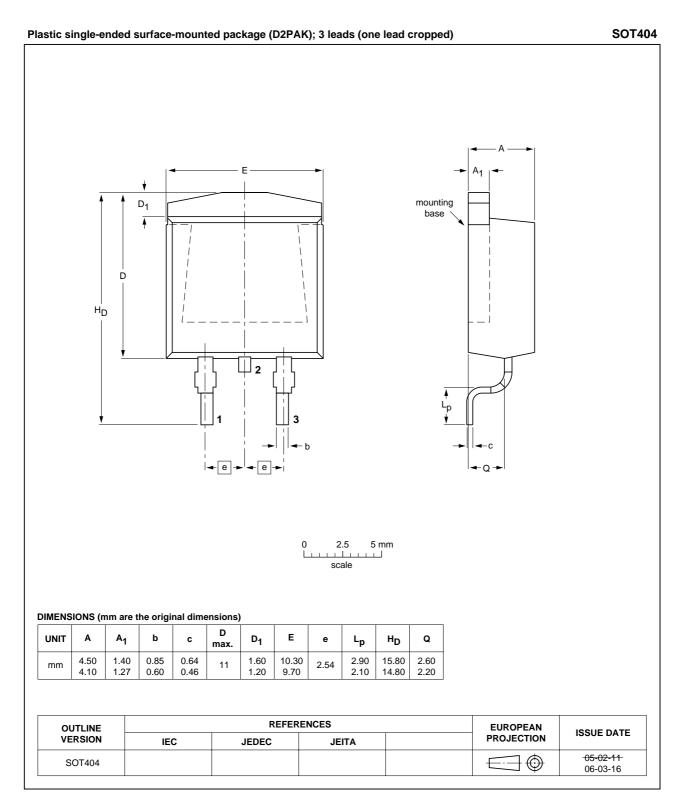


Fig 12. Package outline SOT404 (D2PAK)

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9. Revision history

Table 7. Revision history	у			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BTA316B_SER_B_C_E_1	20070419	Product data sheet	-	-

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10. Legal information

10.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[2] The term 'short data sheet' is explained in section "Definitions".

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